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9/19/02

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
TAKAO NOGUCHI ET AL : EXAMINER: SONG, M. J.
SERIAL NO: 09/842,802 :
FILED: APRIL 27, 2001 : GROUP ART UNIT: 1765
FOR: MULTILAYER THIN FILM AND :
ITS FABRICATION PROCESS AS
WELL AS ELECTRON DEVICE

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Official Action of June 25, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend Claim 1 as in the attached marked-up copy to read as follows:

500B1
A1
1. (Amended) A multilayer thin film formed on an Si substrate by epitaxial growth,
which comprises:
a buffer layer formed on said Si substrate, which said buffer layer includes an oxide
thin film,
a perovskite oxide thin film formed on said buffer layer, which film has a (100) or
(001) orientation, and

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